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OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)						
M)	AR	H. Koga et al., "Two-Dimensional Borderless Contact Pad Technology for a 0.135μm² 4-Gigabit DRAM Cell," ©1997 IEEE, pp. 2.1.1-2.1.3				
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	LR	S. Yamakawa, et al., "Drivability Improvement on Deep-Submicron MOSFET's by Elevation of Source/Drain Regions," IEEE Electron Device Letters, Vol. 20, No. 7, July 1999, pp. 366-368.				
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